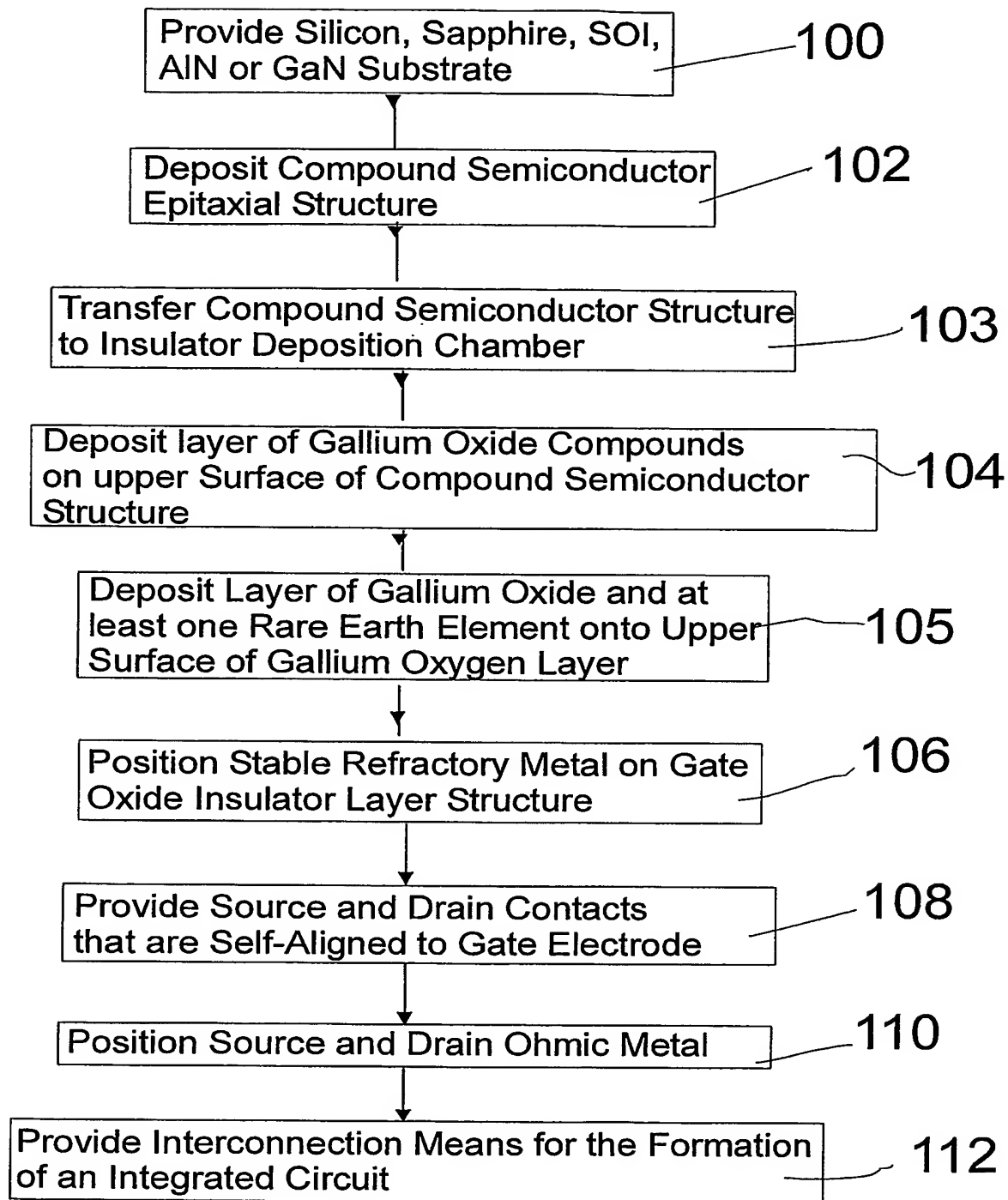


Figure 1

**Figure 2**

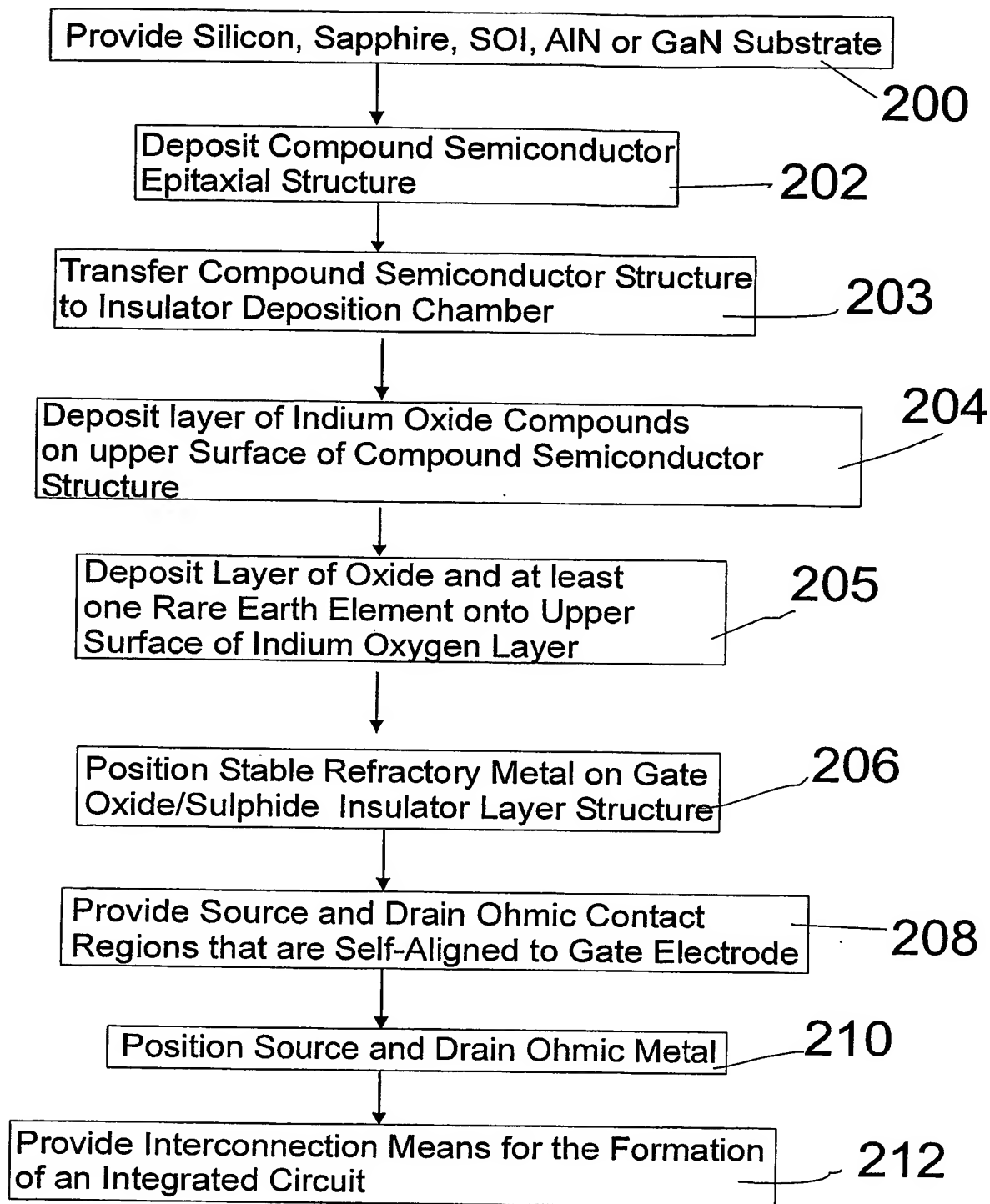


Figure 3

Layer	Thickness	Doping	Description	Comment
6	120	-	Gate-Oxide	
5	4	-	GaN	
4	300	n=1E18	AlGaN	x=0.20
3	500	n=2E17	InGaN	x=0.03
2	8000	-	GaN	buffer
1	500	-	AlN	buffer

Figure 4

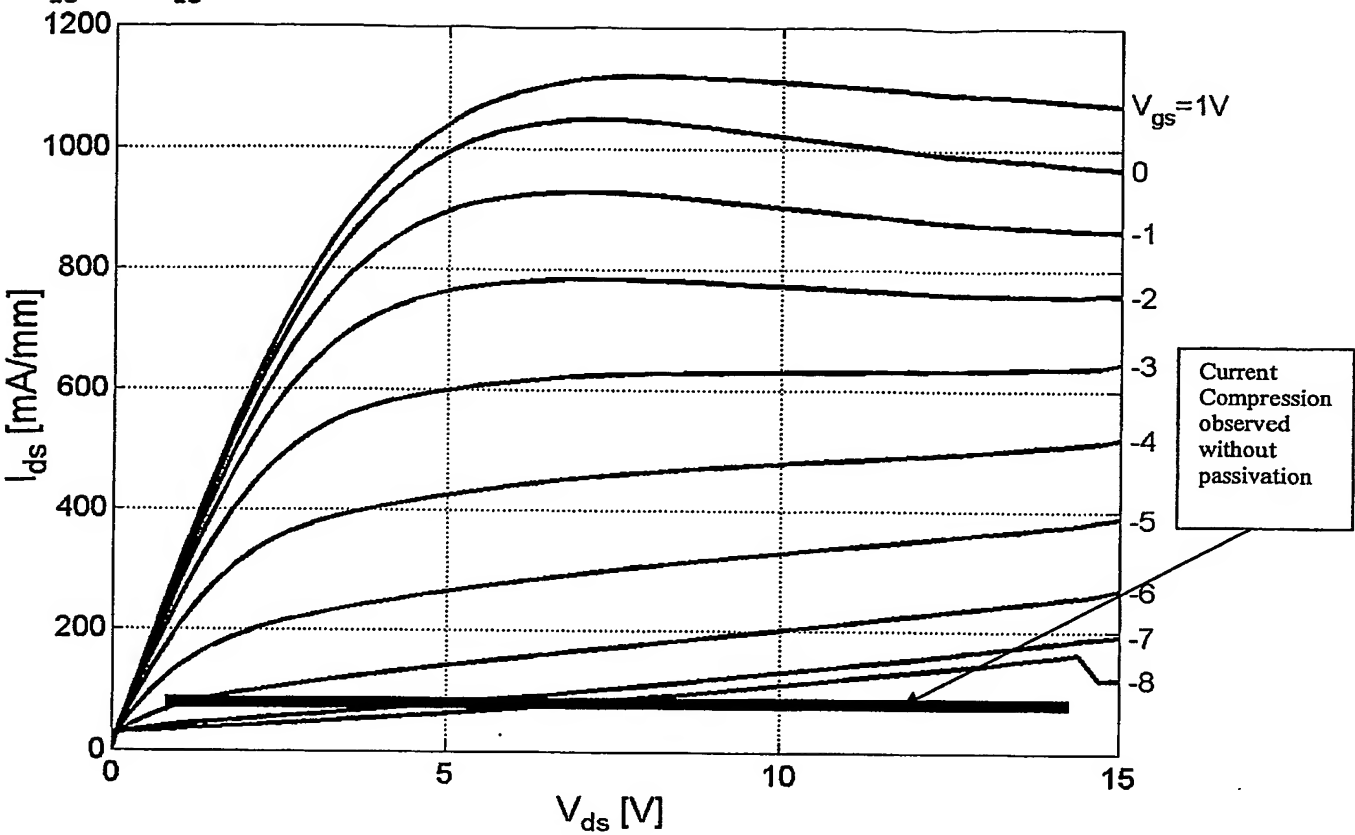


Figure 5

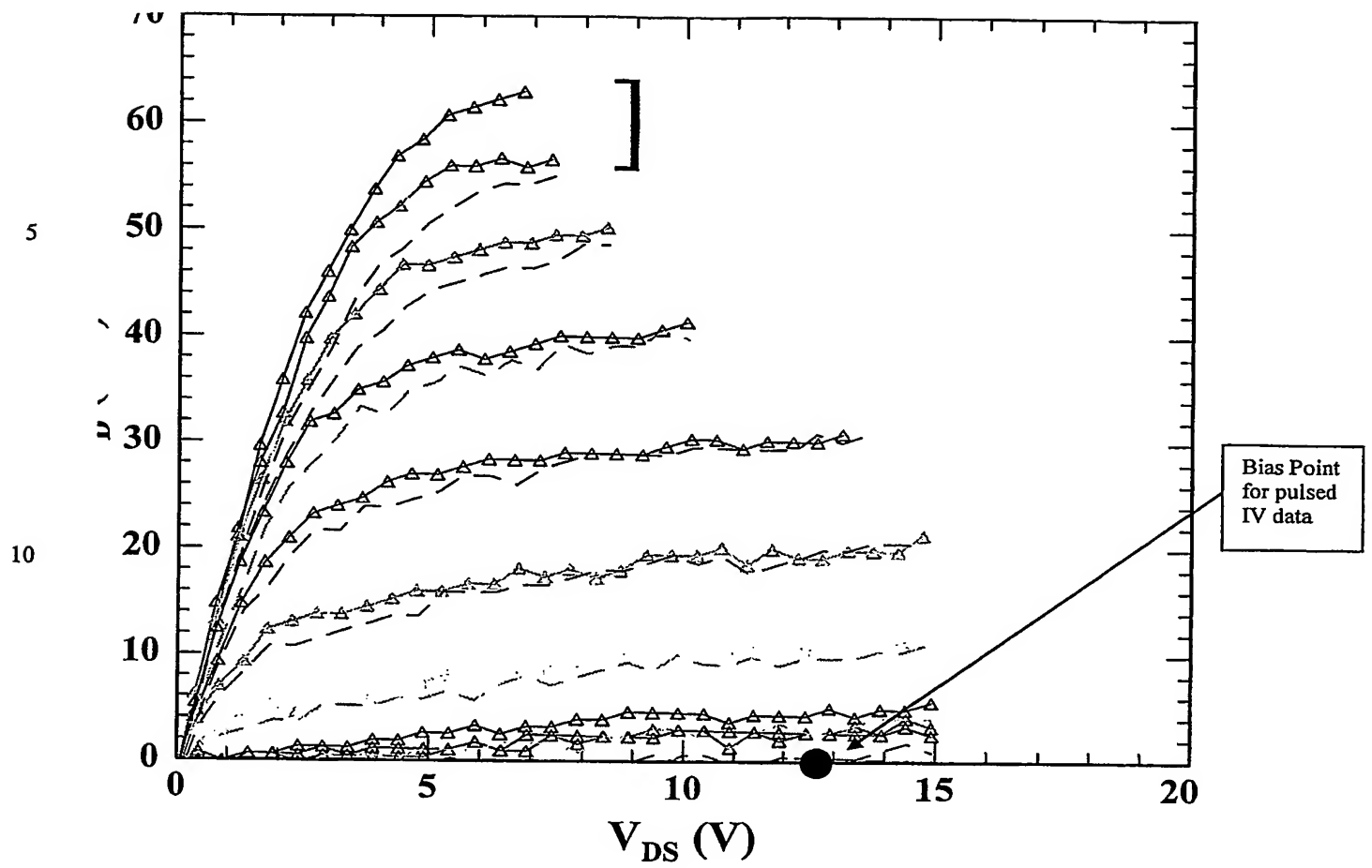


Figure 6

Layer	Thickness	Doping	Description	Comment
6	120	-	Gate-Oxide	
5	40	d-doped	AlN	
4	200	n=1E18	AlGaN	x=0.90
3	5000	-	AlN	buffer
2	<500	-	AlN	Nucleation layer
1		-	AlN	substrate

Figure 7